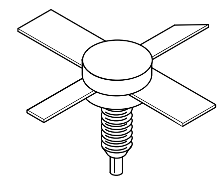
The RF Line
Microwave Pulse Power Transistors

MRF1015MA
MRF1015MB

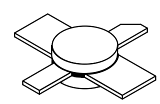
**15 W (PEAK), 960–1215 MHz
MICROWAVE POWER
TRANSISTORS
NPN SILICON**

. . . designed for Class B and C common base amplifier applications in short and long pulse TACAN, IFF, DME, and radar transmitters.

- Guaranteed Performance @ 1090 MHz, 50 Vdc
  Output Power = 15 Watts Peak
  Minimum Gain = 10 dB
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Industry Standard Package
- Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input Matching for Broadband Operation
- Circuit board photomaster available upon request by contacting
  RF Tactical Marketing in Phoenix, AZ.



**CASE 332–04, STYLE 1
MRF1015MA**



**CASE 332A–03, STYLE 1
MRF1015MB**

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	60	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Device Dissipation @ T_C = 25°C (1) Derate above 25°C	P_D	17.5 100	Watts mW/°C
Storage Temperature Range	T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	10	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

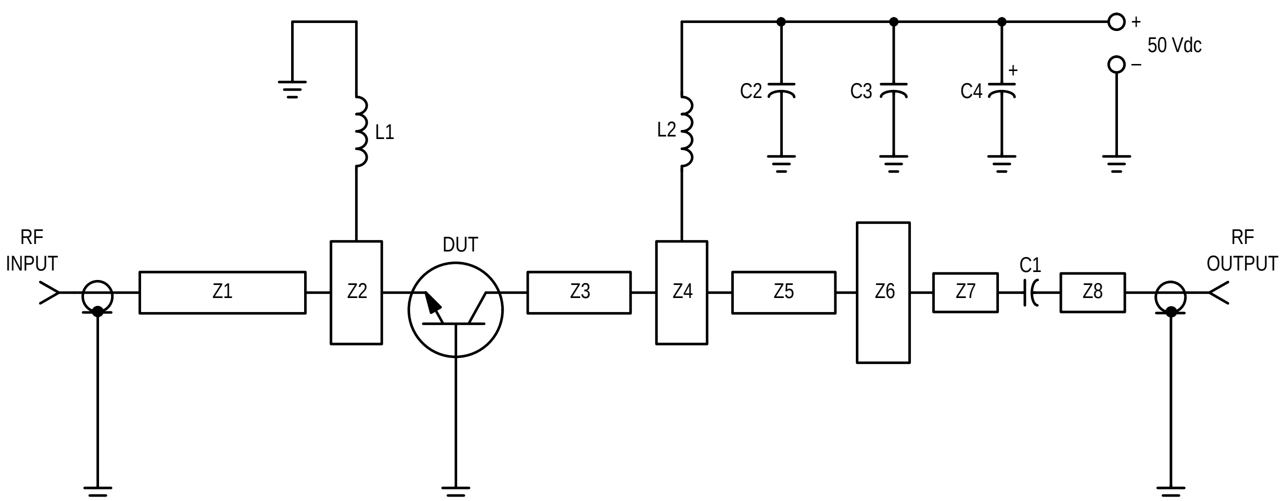
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 10 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	60	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 10 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 1.0 mAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 50 Vdc, I_E = 0)	I_{CBO}	—	—	1.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 250 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	10	40	100	—

NOTES:
1. These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

(continued)

ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 50 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	5.0	7.5	pF
FUNCTIONAL TESTS (Pulse Width = 10 µs, Duty Cycle = 1.0%)					
Common–Base Amplifier Power Gain (V_{CC} = 50 Vdc, P_{out} = 15 W Peak, f = 1090 MHz)	G_{PB}	10	12.5	—	dB
Collector Efficiency (V_{CC} = 50 Vdc, P_{out} = 15 W Peak, f = 1090 MHz)	η	30	35	—	%
Load Mismatch (V_{CC} = 50 Vdc, P_{out} = 15 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	ψ	No Degradation in Power Output			



C1, C2 — 220 pF 100 mil Chip Capacitor
C3 — 0.1 µF
C4 — 47 µF/75 V Electrolytic Capacitor
L1, L2 — 3 Turns #18 AWG, 1/8″ ID
Z1–Z8 — Microstrip, See Photomaster
Board Material — 0.032″ Glass Teflon
ε_r = 2.5

Figure 1. 1090 MHz Test Circuit

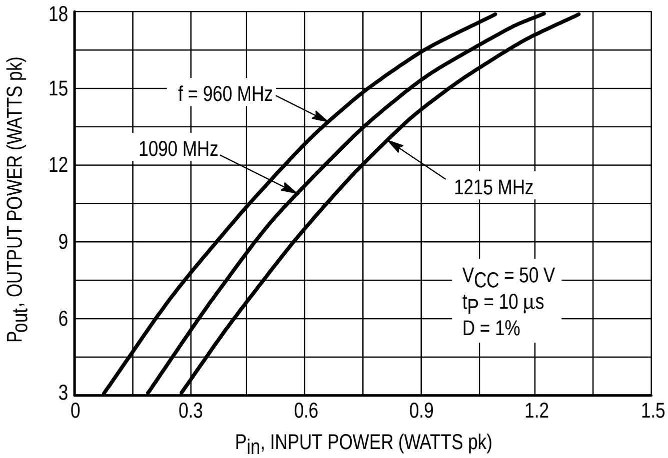


Figure 2. Output Power versus Input Power

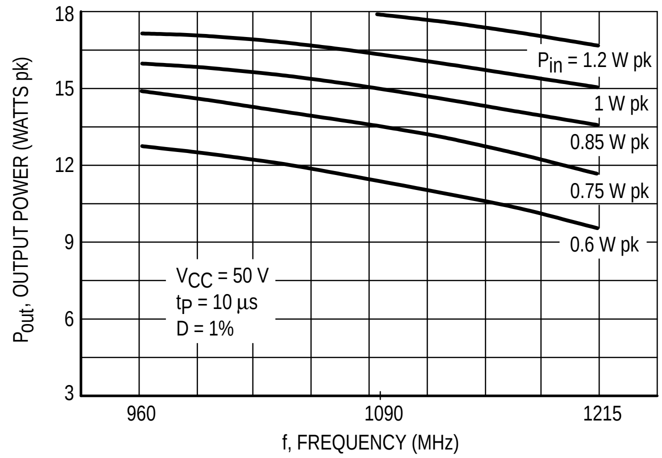


Figure 3. Output Power versus Frequency

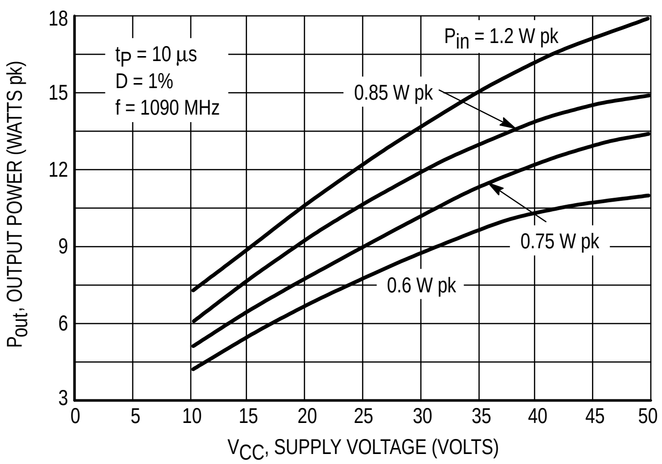


Figure 4. Output Power versus Supply Voltage

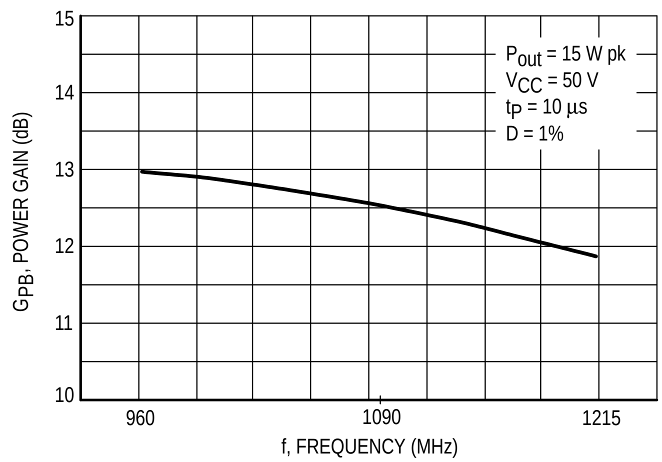
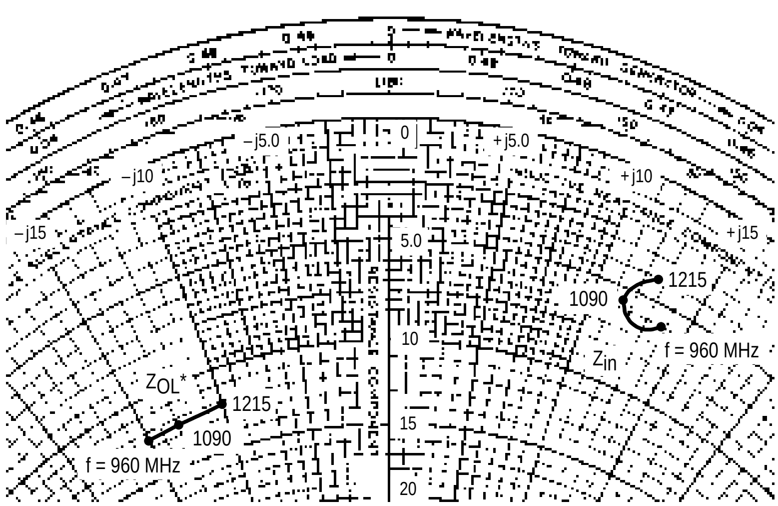


Figure 5. Power Gain versus Frequency



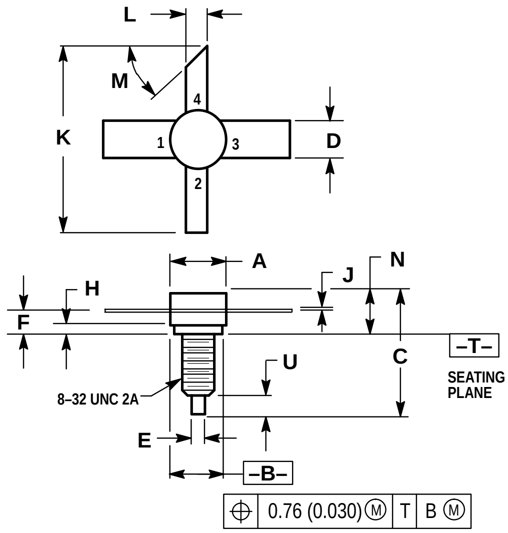
P_{out} = 15 W pk V_{CC} = 50 V
t_p = 10 µs D = 1%

f MHz	Z_{in} Ohms	Z_{OL}* Ohms
960	5.9 + j13.6	12.5 – j15
1090	5.5 + j11.5	12.4 – j12.8
1215	4.0 + j12.5	12.1 – j10

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.

Figure 6. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS

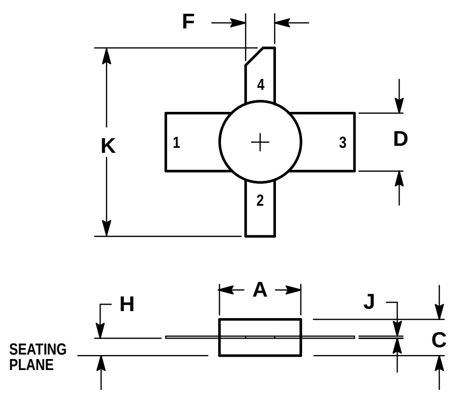


NOTES:
1. DIMENSION K APPLIES TWO PLACES.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1973.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	6.86	7.62	0.270	0.300
B	6.10	6.60	0.240	0.260
C	16.26	16.76	0.640	0.660
D	4.95	5.21	0.195	0.205
E	1.40	1.65	0.055	0.065
F	2.67	4.32	0.105	0.170
H	1.40	1.65	0.055	0.065
J	0.08	0.18	0.003	0.007
K	15.24	—	0.600	—
L	2.41	2.67	0.095	0.105
M	45 °NOM		45 °NOM	
N	4.97	6.22	0.180	0.245
U	2.92	3.68	0.115	0.145

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR

CASE 332–04
ISSUE D
MRF1015MA



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.270	0.290	6.86	7.36
C	0.115	0.135	2.93	3.42
D	0.195	0.205	4.96	5.20
F	0.095	0.105	2.42	2.66
H	0.050	0.070	1.27	1.77
J	0.003	0.007	0.08	0.17
K	0.600	—	15.24	—

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR

CASE 332A–03
ISSUE D
MRF1015MB

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